

	Hit s	Search Text	DBs
39	41	((substrate or wafer) same (resist or photoresist) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4)) and (develop\$4 same (pattern or mask) same (plat\$4 or metalliz\$5)) and ((plat\$4 or metallization) same strip\$4 same (base or basic or developer)) and ((ITO or (indium near4 tin near4 oxide)) same (pattern\$5 or photolithograph\$4 or lithograph\$5))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
40	169	((substrate or wafer) same (resist or photoresist) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4)) and (develop\$4 same (pattern or mask) same (plat\$4 or metalliz\$5)) and ((plat\$4 or metallization) same (remov\$5 or strip\$4) same (mask\$5 or pattern or resist) same (base or basic or developer)) and ((ITO or (indium near4 tin near4 oxide)) same (pattern\$5 or photolithograph\$4 or lithograph\$5))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
41	160	((substrate or wafer) same (resist or photoresist) same (lithography or expos\$4 or irradiat\$4 or illuminat\$4)) and (develop\$4 same (pattern or mask) same (plat\$4 or metalliz\$5)) and ((plat\$4 or metallization) same (remov\$5 or strip\$4) same (mask\$5 or pattern) same (base or developer)) and ((ITO or (indium near4 tin near4 oxide)) same (pattern\$5 or photolithograph\$4 or lithograph\$5))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB